L Number	Hits	Search Text	DB	Time stamp
1	3	"18249"	EPO; JPO;	2003/11/18 14:56
,-			DERWENT	
2	669	miyakawa.in.	EPO; JPO; DERWENT	2003/11/18 14:56
	10	miyakawa.in. and plasma	EPO; JPO;	2003/11/18 15:01
3	10	miyakawa.in. and piasma	DERWENT	2000/11/10 10:01
4	26	barnes-michael.in. cox-michael-s\$.in.	EPO; JPO;	2003/11/18 15:02
1		lai-canfeng.in. parks-joun.in.	DERWENT	
5	58	barnes-michael.in. cox-michael-s\$.in.	USPAT;	2003/11/18 15:02
	^	lai-canfeng.in. parks-joun.in.	US-PGPUB USPAT;	2003/05/13 11:25
-	0	(((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and	US-PGPUB	2003/03/13 11:23
] [((anneal\$3 heat\$s) with silylation with	00 10100	1
		cur\$3)		
_	0	(((118/719) or (156/345.31) or	USPAT;	2003/05/13 11:32
		(156/345.32) or (414/939)).CCLS.) and	US-PGPUB	
		((anneal\$3 heat\$s) same silylation same cur\$3)		
_	1	09/502,126	USPAT;	2003/05/13 11:23
		0373027120	US-PGPUB	
-	3534	atmospher\$3 with pressure with plasma	USPAT;	2003/05/13 11:26
		4554045	US-PGPUB	2002/05/12 12:24
-	1709	((118/719) or (156/345.31) or (156/345.32)	USPAT; US-PGPUB	2003/05/13 12:34
_	50	or (414/939)).CCLS. (atmospher\$3 with pressure with plasma)	USPAT;	2003/05/13 11:26
-	50	and (((118/719) or (156/345.31) or	US-PGPUB	
		(156/345.32) or (414/939)).CCLS.)		
-	6	5578130.URPN.	USPAT	2003/05/13 11:30
-	3	(((118/719) or (156/345.31) or	USPAT;	2003/05/13 11:34
		(156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) same silicon same	US-PGPUB	
		cur\$3)		ı
_	49	(cur\$3 with chamber) and (anneal\$3 with	USPAT;	2003/05/13 12:17
		chamber) and ((silicon silylation) with	US-PGPUB	
	_	chamber)		2002/05/12 11:57
-	8	("4944895" "5047369" "5858457" "5958577" "6048804" "6153511"	USPAT	2003/05/13 11:57
		"6218302" "6284682").PN.		
_	1	"high pressure deposition module"	USPAT;	2003/05/13 12:33
			US-PGPUB	
-	1374	"APCVD"	USPAT;	2003/05/13 12:39
	17	"APCVD" and (((118/719) or (156/345.31) or	US-PGPUB USPAT;	2003/05/13 12:34
-	1 /	(156/345.32) or (414/939)).CCLS.)	US-PGPUB	2003/03/13 12.31
-	464	"APCVD" with plasma	USPAT;	2003/05/13 12:42
		-	US-PGPUB	
-	1	("APCVD" with plasma) and (((118/719) or	USPAT;	2003/05/13 12:39
•		(156/345.31) or (156/345.32) or	US-PGPUB	
_	9	(414/939)).CCLS.) "silylation chamber"	USPAT;	2003/05/13 12:44
			US-PGPUB	
-	44	silylation with chamber	USPAT;	2003/05/13 12:44
[0.5	/	US-PGPUB	2003/05/13 13:05
-	35	(silylation with chamber) not "silylation chamber"	USPAT; US-PGPUB	2003/03/13 13:05
_	1	("6451118").PN.	USPAT;	2003/05/13 13:05
	-		US-PGPUB	
-	1667	spin with coating with uniform\$3	USPAT;	2003/05/13 15:34
			US-PGPUB	2002/05/12 15:27
-	5	(spin with coating with uniform\$3) and (((118/719) or (156/345.31) or	USPAT; US-PGPUB	2003/05/13 15:37
		(((118/719) of (136/343.31) of (156/345.32) or (414/939)).CCLS.)	35 13105	
-	0	spin with coating with uniform\$3 with	USPAT;	2003/05/13 15:35
		atmoshperic with deposit\$3	US-PGPUB	0000/05/10 05 05
-	0	spin with coating with uniform\$3 same (USPAT;	2003/05/13 15:36
[_	162	atmoshperic with deposit\$3) (spin with coating with uniform\$3) and	US-PGPUB USPAT;	2003/05/13 15:40
	102	(118/\$.ccls.)	US-PGPUB	2505, 52, 25
-	4	(spin with coating with uniform\$3 with	USPAT;	2003/05/13 15:40
		atmospheric) and (118/\$.ccls.)	US-PGPUB	

				TRO TRO	2002/11/10 11-15
-	•	3584	plasma with (atmospheric high) with	EPO; JPO; DERWENT	2003/11/18 11:15
			pressure	EPO; JPO;	2003/11/18 11:29
-	ļ	1257	plasma with (atmospheric high) with	DERWENT	2003/11/10 11:23
	j		pressure with (coat\$3 deposit\$3 layer	DEKMENI	
			film)	BBO TDO	2002/11/10 11:30
-		380	(plasma with (atmospheric high) with	EPO; JPO;	2003/11/18 11:30
}			pressure with (coat\$3 deposit\$3 layer	DERWENT	
ļ			film)) and c23c016\$.ipc.		
_		135	(plasma with (atmospheric) with pressure	EPO; JPO;	2003/11/18 12:17
			with (coat\$3 deposit\$3 layer film)) and	DERWENT	
			c23c016\$.ipc.		
-		30	(plasma with (atmospheric) with pressure	EPO; JPO;	2003/11/18 11:20
			with (coat\$3 deposit\$3 layer film) with	DERWENT	
			(semiconductor dielectric)) and		
			c23c016\$.ipc.		
1 -		3232	plasma with (atmospheric high) with	USPAT;	2003/11/18 11:29
			pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
			film)		İ
-		20	(plasma with (atmospheric high) with	EPO; JPO;	2003/11/18 12:59
			pressure with (coat\$3 deposit\$3 layer	DERWENT	
			film)) and 118/\$.ccls.		
_		330	(plasma with (atmospheric high) with	USPAT;	2003/11/18 12:59
1			pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
1			film)) and 118/\$.ccls.	!	
-		2	(plasma with (atmospheric high) with	USPAT;	2003/11/18 11:31
			pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
			film)) and 414/\$.ccls.		
-		135	(plasma with (atmospheric high) with	USPAT;	2003/11/18 11:31
			pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
			film)) and 156/345.\$.ccls.		
-		41	(plasma with (atmospheric high) with	USPAT;	2003/11/18 11:31
		İ	pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
			film)) and 118/719.ccls.		0000/11/10 11 50
-		1	("5319247").PN.	USPAT;	2003/11/18 11:53
				US-PGPUB	0000/11/10 11:45
-		33	5319247.URPN.	USPAT	2003/11/18 11:45
-		1154	"atmospheric pressure" with plasma with	USPAT;	2003/11/18 11:54
			(deposit\$3 coat\$3 film layer)	US-PGPUB	2002/11/10 11-54
-		376	"atmospheric pressure" with plasma with	EPO; JPO;	2003/11/18 11:54
1			(deposit\$3 coat\$3 film layer)	DERWENT	2003/11/18 11:54
-		34	("atmospheric pressure" with plasma with	EPO; JPO; DERWENT	2003/11/10 11:34
			(deposit\$3 coat\$3 film layer)) same	DELMENT	
		015	semiconductor ("atmospheric pressure" with plasma with	USPAT;	2003/11/18 11:59
-		215		US-PGPUB	2003/11/10 11:03
-		1	(deposit\$3 coat\$3 film layer)) same	00 10500	
		330	semiconductor (plasma with (atmospheric high) with	USPAT;	2003/11/18 12:17
-		330		US-PGPUB	2003/11/10 12:11
			pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.ccls.	00 19100	
		2	(in\$1line same cluster) and c23c016\$.ipc.	EPO; JPO;	2003/11/18 12:18
-		2	(Institute same cruster) and crocolog.ipc.	DERWENT	
		9	(in\$1line same cluster) and 118/719.ccls.	USPAT;	2003/11/18 12:18
-			(Thytithe Same Cluster, and 110//19.0015.	US-PGPUB	=====================================
_		2.4	(plasma with "atmospheric pressure") and	USPAT;	2003/11/18 13:53
-		24	118/719.ccls.	US-PGPUB	
_		18	5651867.URPN.	USPAT	2003/11/18 13:07
_		1	("6342275").PN.	USPAT;	2003/11/18 14:56
-			(00122/0).110.	US-PGPUB	
L				100 10200	<u> </u>